

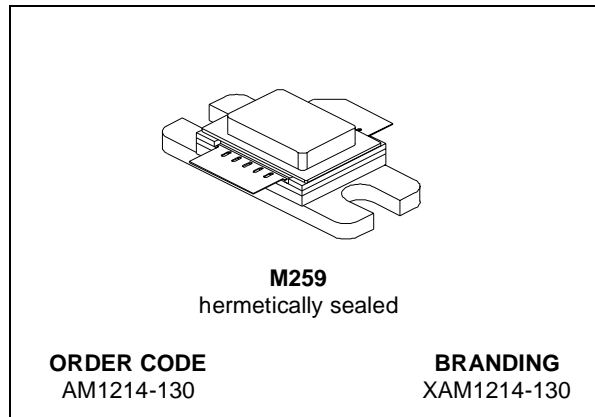


AM1214-130

RF POWER TRANSISTORS L-BAND RADAR APPLICATIONS

TARGET DATA

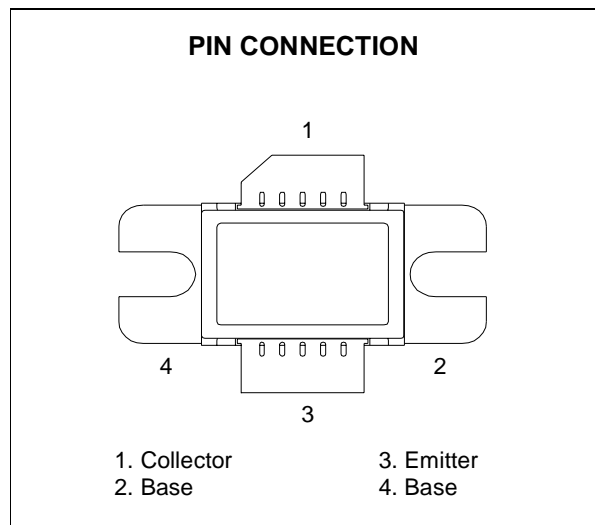
- REFRACTORY /GOLD METALLIZATION
- EMITTER SITE BALLASTING
- LOW RF THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 130$ W MIN. WITH 8.0 dB GAIN
- 1215-1400 MHz OPERATION



DESCRIPTION

The AM1214-130 is a rugged, Class C common base device designed as driver of AM1214-250 for new L - Band medium & long pulse radar applications.

Minimal amplitude droop over a long pulse of 500 microsec. is guaranteed by a thermal design incorporating an overlay site-ballasted die geometry.



ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation ($T_C \leq 85^{\circ}C$)*	TBD	W
I_C	Device Current*	12	A
V_{CBO}	Collector-Base Voltage	70	V
T_j	Operating Junction Temperature	+250	$^{\circ}C$
T_{STG}	Storage Temperature	-65 to +200	$^{\circ}C$

THERMAL DATA

$R_{th(j-c)}$	Junction -Case Thermal Resistance*	TBD	$^{\circ}C/W$
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* Applies only to rated RF amplifier operation: 150 microsec / 10%

ELECTRICAL SPECIFICATION ($T_{CASE} = 25^{\circ}C$)

STATIC

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
BV_{CBO}	$I_C = 20\text{ mA}$	$I_E = 0\text{ mA}$	70			V
BV_{CES}	$I_C = 20\text{ mA}$	$V_{BE} = 0\text{ V}$	70			V
BV_{EBO}	$I_E = 10\text{ mA}$	$I_C = 0\text{ mA}$	3.5			V
I_{CES}	$V_{CE} = 40\text{ V}$	$V_{BE} = 0\text{ V}$			5	mA
h_{FE}	$V_{CE} = 5\text{ V}$	$I_C = 0.25\text{ A}$	10			

DYNAMIC @ 150 MICROSEC / 10 %

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
P_{OUT}	$f = 1215 - 1400\text{ MHz}$	$P_{IN} = 20\text{ W}$	$V_{CC} = 50\text{ V}$	130	160		W
η_C	$f = 1215 - 1400\text{ MHz}$	$P_{IN} = 20\text{ W}$	$V_{CC} = 50\text{ V}$	40	45		%
G_P	$f = 1215 - 1400\text{ MHz}$	$P_{IN} = 20\text{ W}$	$V_{CC} = 50\text{ V}$	8.1	9.0		dB

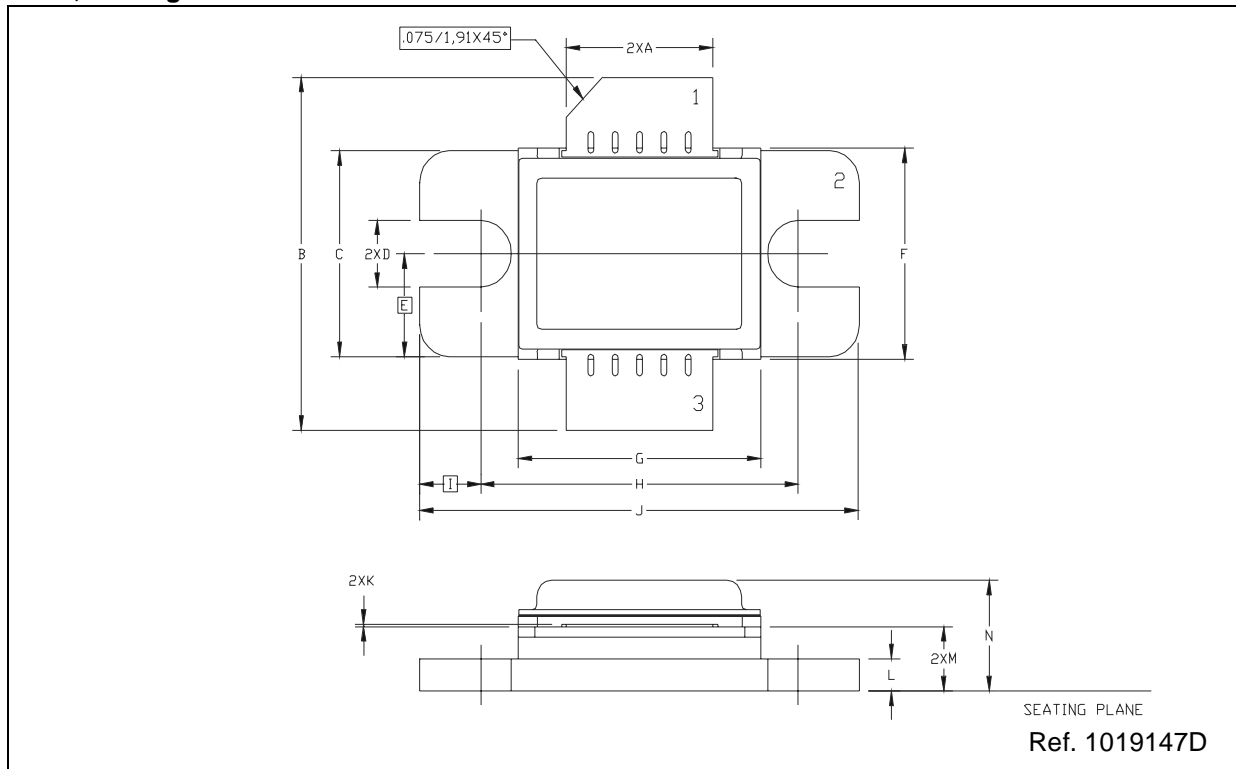
DYNAMIC @ 500 MICROSEC / 10 %

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
P_{OUT}	$f = 1215 - 1400\text{ MHz}$	$P_{IN} = 20\text{ W}$	$V_{CC} = 50\text{ V}$	110	140		W
η_C	$f = 1215 - 1400\text{ MHz}$	$P_{IN} = 20\text{ W}$	$V_{CC} = 50\text{ V}$	40	45		%
G_P	$f = 1215 - 1400\text{ MHz}$	$P_{IN} = 20\text{ W}$	$V_{CC} = 50\text{ V}$	7.4	8.45		dB

M259 (.400 x .500 SUPER WIDE 2/L HERM. W/FLG) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A	7.49		7.75	.295		.305
B	19.56		21.08	.770		.830
C	9.65		9.91	.380		.390
D	3.18		3.43	.125		.135
E		4.90			.193	
F	10.03		10.34	.395		.407
G	12.45		12.95	.490		.510
H	16.38		16.64	.645		.655
I		3.18			.125	
J	22.61		23.11	.890		.910
K	0.05		0.15	.002		.006
L	1.40		1.65	.055		.065
M	2.79		3.30	.110		.130
N			5.84			.230

M259, Package Outline



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